

A High-Efficiency Transformer-in-Package Isolated DC-DC Converter Using Glass-Based Fan-Out Wafer-Level Packaging

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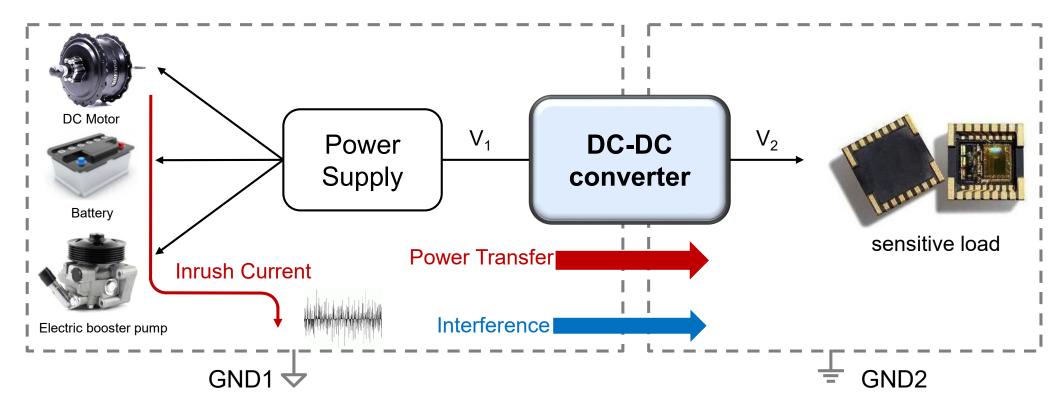
University of Science and Technology of China (USTC)

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Outline

- Motivation
- Proposed TiP FOWLP Isolated DC-DC converter
 - System Architecture & TiP Solution
 - The Glass-based Transformer
 - Circuit Implementation
- Measurement Results
- Conclusions

Motivation



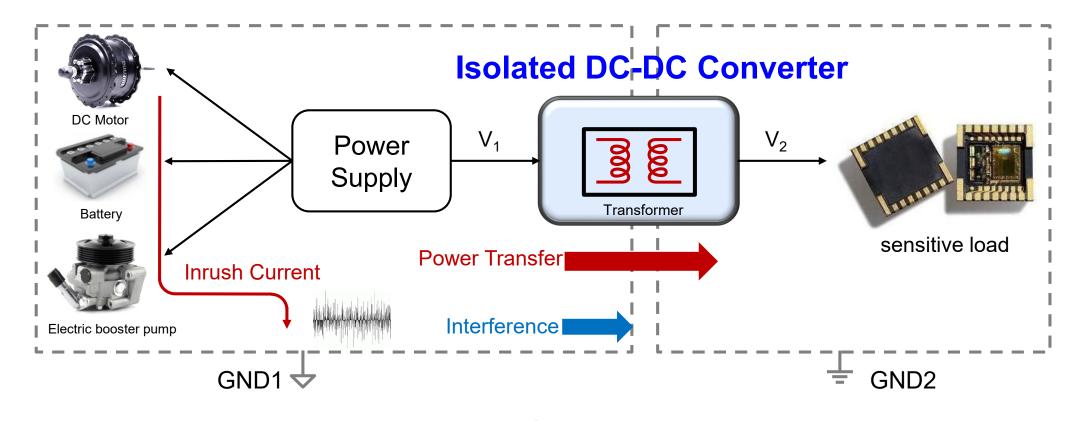
Voltage breakdown

- Potential inrush current

- Common-mode noise
- Human Safety

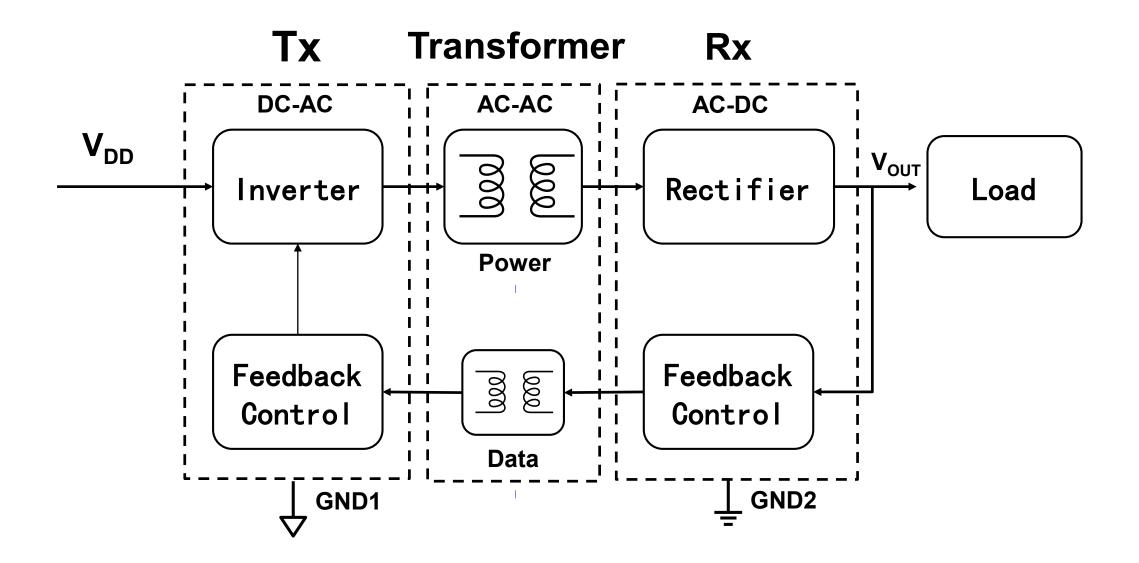


Motivation



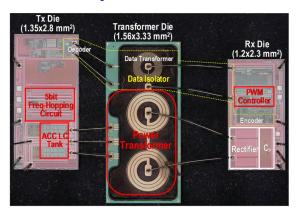
- Device and human safety
- Data acquisition accuracy
- System reliability

Block Diagram



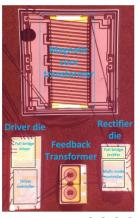
State-of-the-arts

Si-based Gold windings 6µm-thick



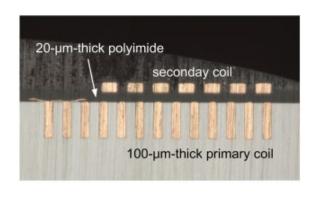
[W. Qin ISSCC'19]

Magnetic-core



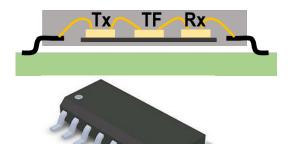
[Y. Zhuo ISSCC'19]

Si-embedded 100µm-Thick



[L. Li ISSCC'20]





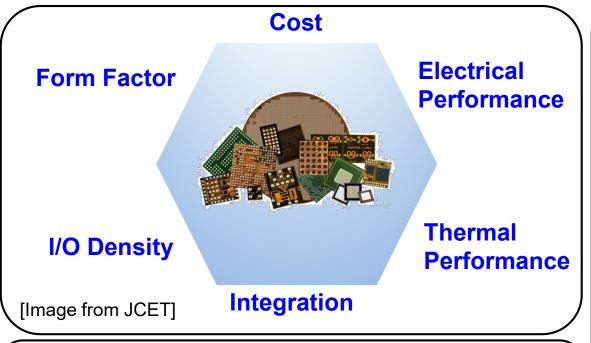
Reference	Freq. (MHz)	Quality factor	Transformer (TF) Size (mm²)	Max. P _{OUT} (W)	Peak Efficiency
W. Qin ISSCC'19	160-210	6.8	5.2	8.0	34%
Y. Zhuo ISSCC'19	16-25	12	8.4	1.1	52%
L. Li ISSCC'20	11	16/7	4	0.165	34%

Design challenges for fully-integrated isolated DC-DC converters

- Trade-off between size, cost and quality factor of transformer for high efficiency
- Compact form factor for high power density

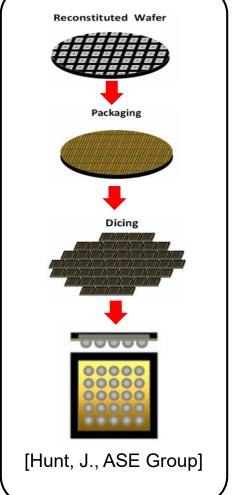
Wafer-Level Packaging

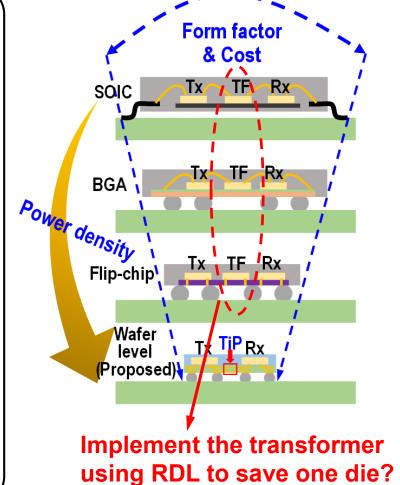
Market drivers & Wafer Level Packaging capabilities





FOWLP process flow

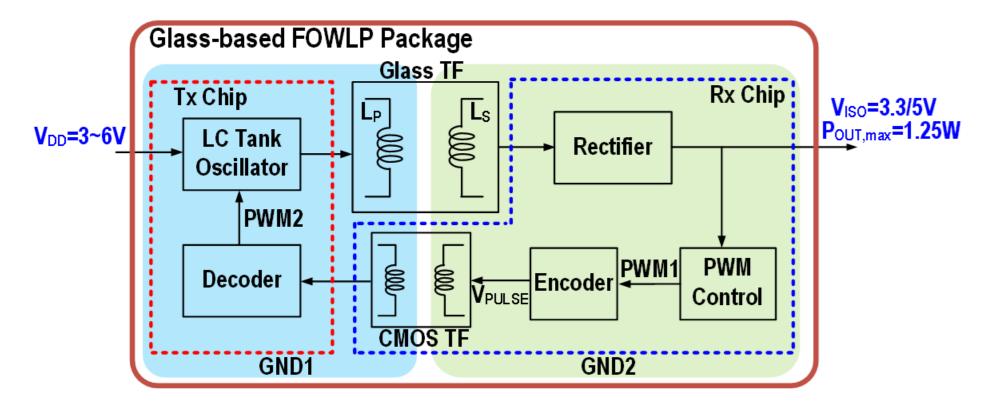




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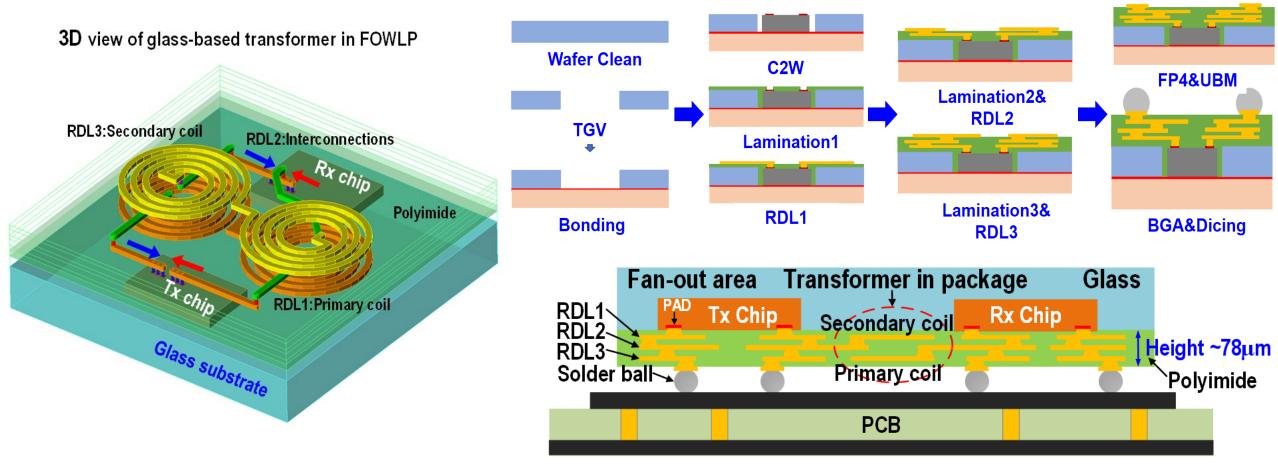
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System Architecture



- Glass-based transformer (TF) in fan-out wafer level packaging (FOWLP)
- TX chip with wide V_{DD} range
- RX chip with on-chip TF for PWM digital isolator

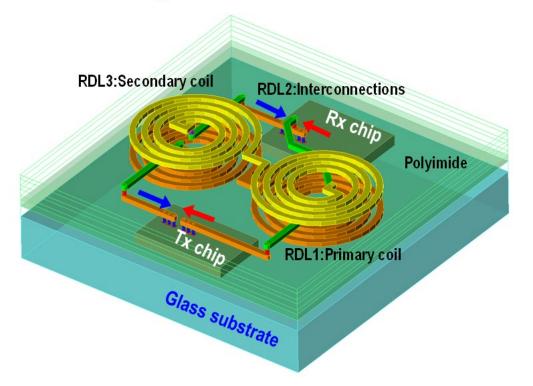
Transformer-in-Package Solution



- The TX and RX chips are planted into the cavities with 300µm in the glass
- 3-RDL for TF and interconnections without extra TF chip

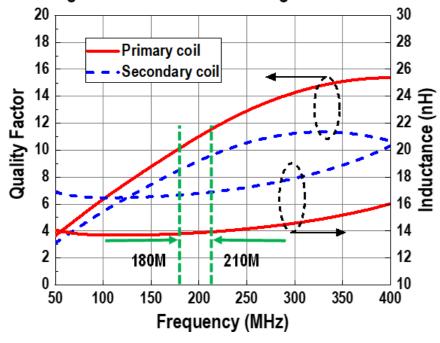
Glass-based Transformer

3D view of glass-based transformer in FOWLP

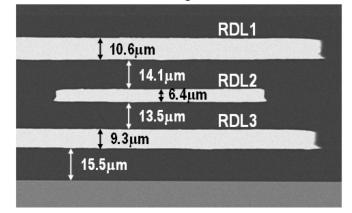


 $Q_p=10.3\sim11.6$ $Q_S=8.6\sim9.6$ $L_p=13.8nH$ $L_S=16.7nH$ @180-210MHz

Electromagnetic-simulated results of glass-based transformer

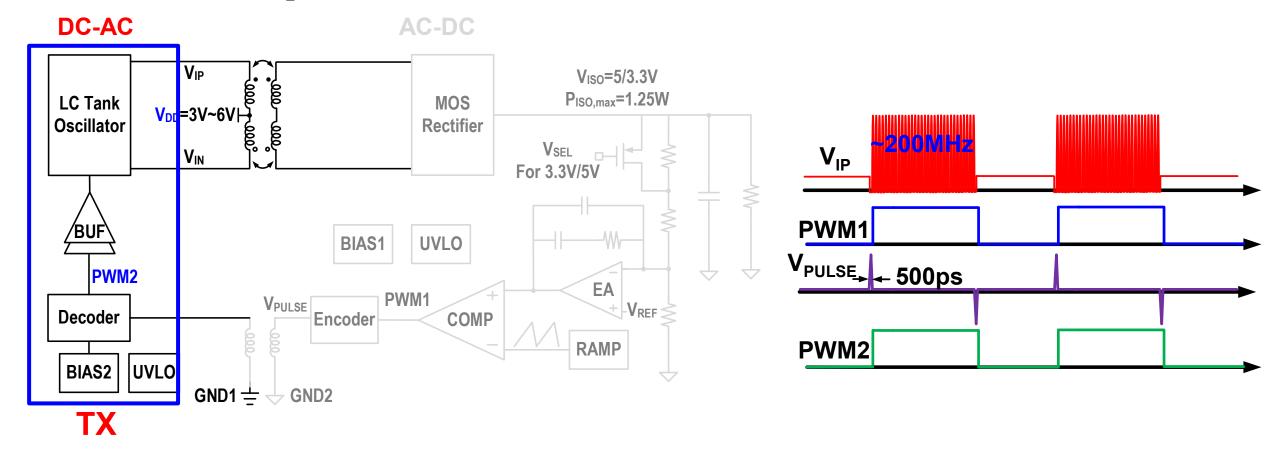


Cross section view of the glass-based transformer



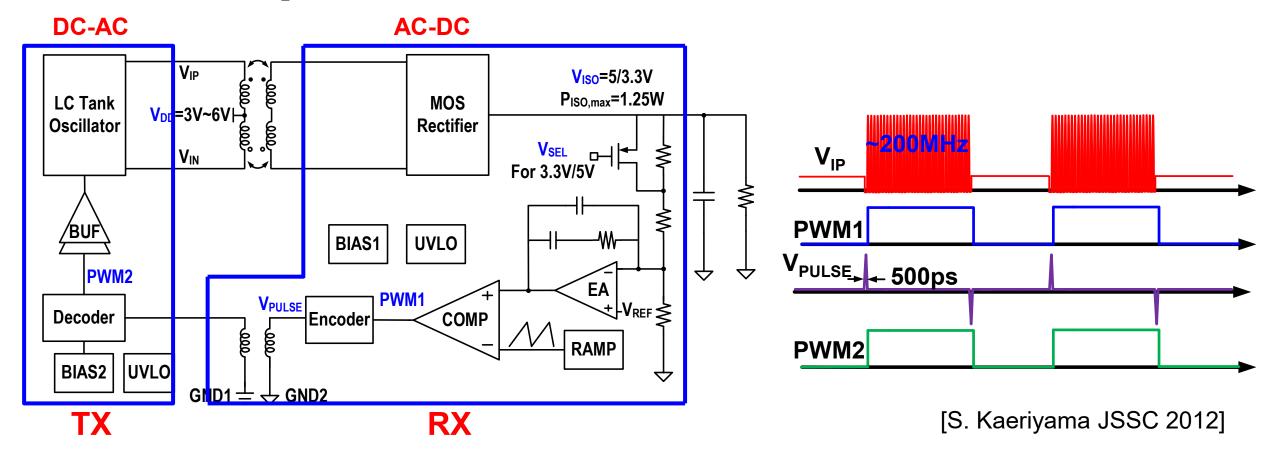
- RDL1 and RDL3 for Primary and Secondary coils: 10-µm thick, 100-µm wide and 3.5 turns of windings
- Simulated coupling factor: 0.8

Circuit Implementation



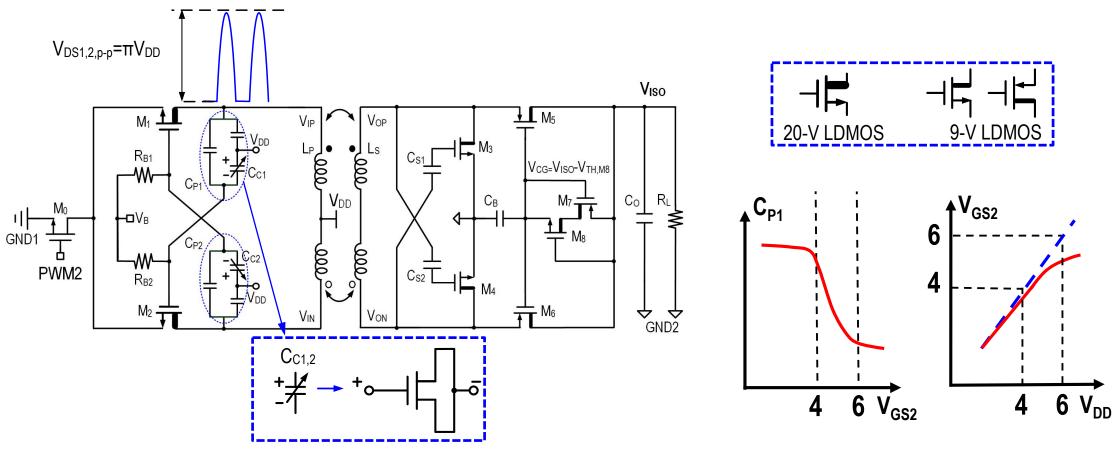
■ LC tank oscillator operated at ~200MHz resonate frequency

Circuit Implementation



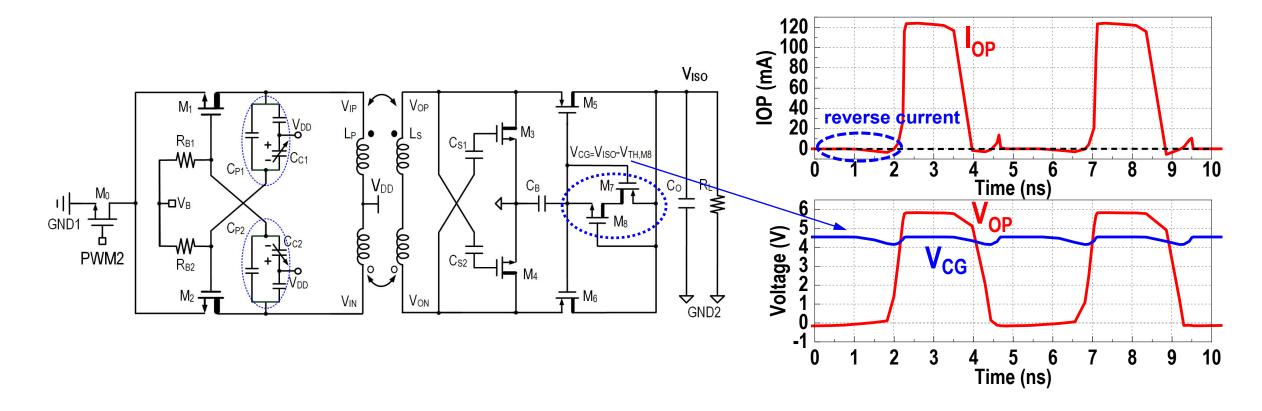
- PWM control with Type-II compensation
- PWM signal running at 625kHz is transmitted from RX to TX via a digital isolator

Power Stage



- 20V LDMOS for power transistor M_{1.2}
- The varactor section for wide supply voltage range of 3~6V

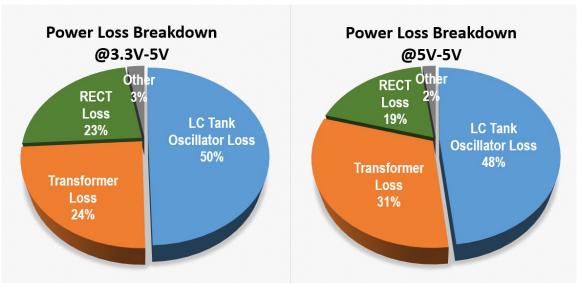
Power Stage



 Fully-bridge MOS rectifier with common-gate bootstrapped for preventing the reverse current

Power Loss Breakdown

Simulated power loss breakdown



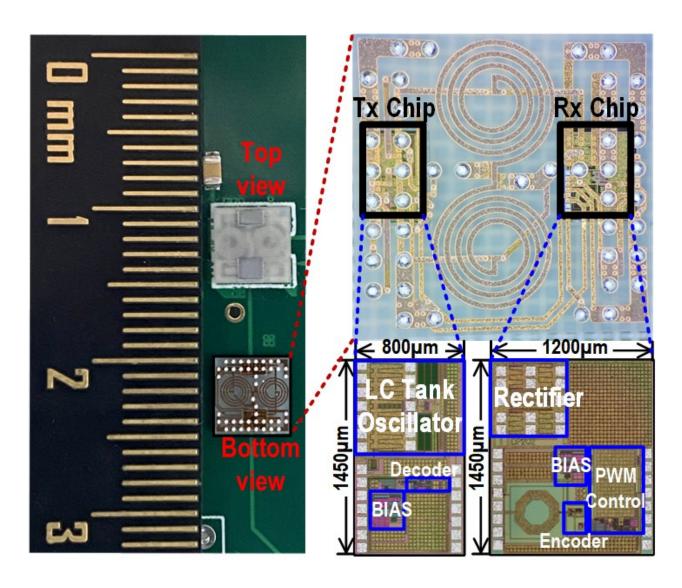
Simulated efficiency

Condition @250mW	η _{LC Tank Osc}	η_{TF}	η _{Rectifier}	η _{Overall}
3.3V-5V	75.6%	84.1%	82%	52.1%
5V-5V	73.5%	76.7%	82%	46.2%

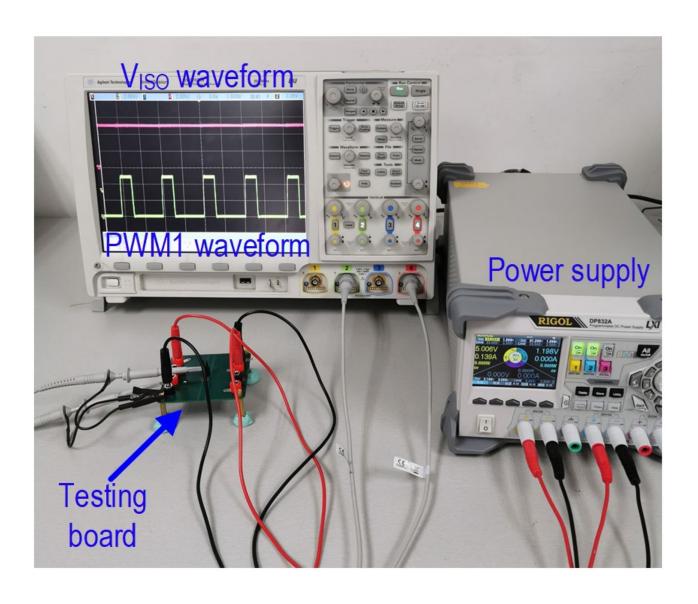
- Simulated power loss breakdown of the proposed converter
- Increased loss of TF results in reduced efficiency of TF at 5V-5V mode

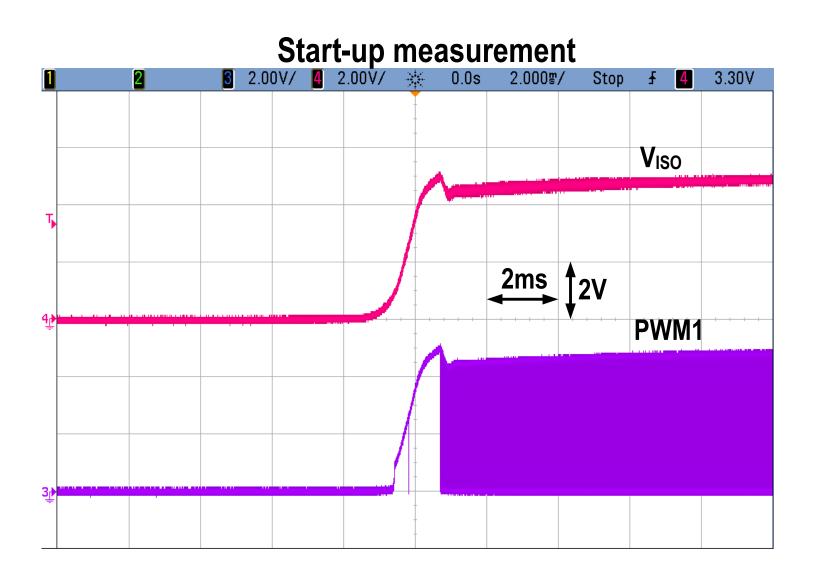
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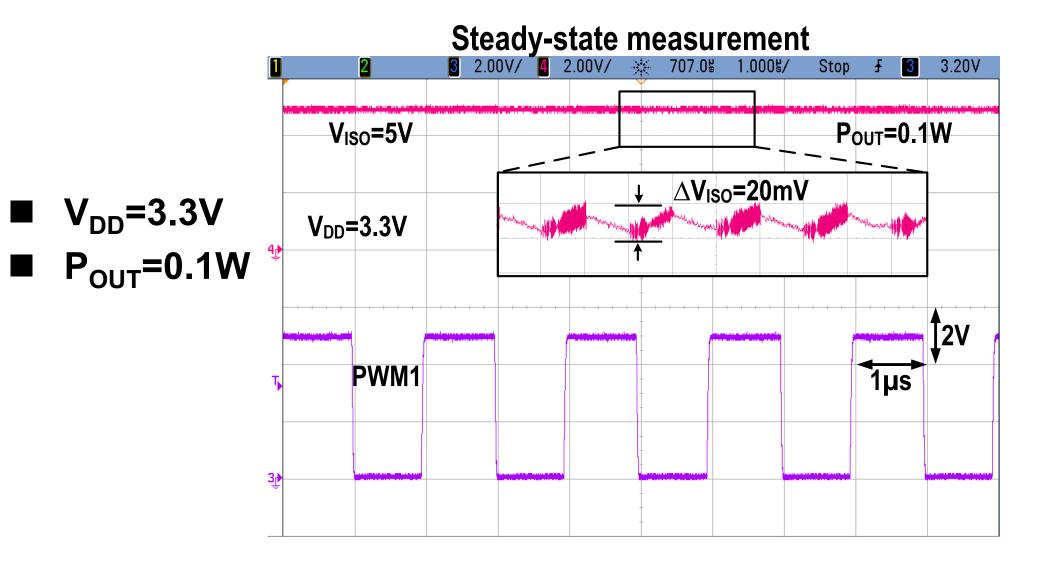
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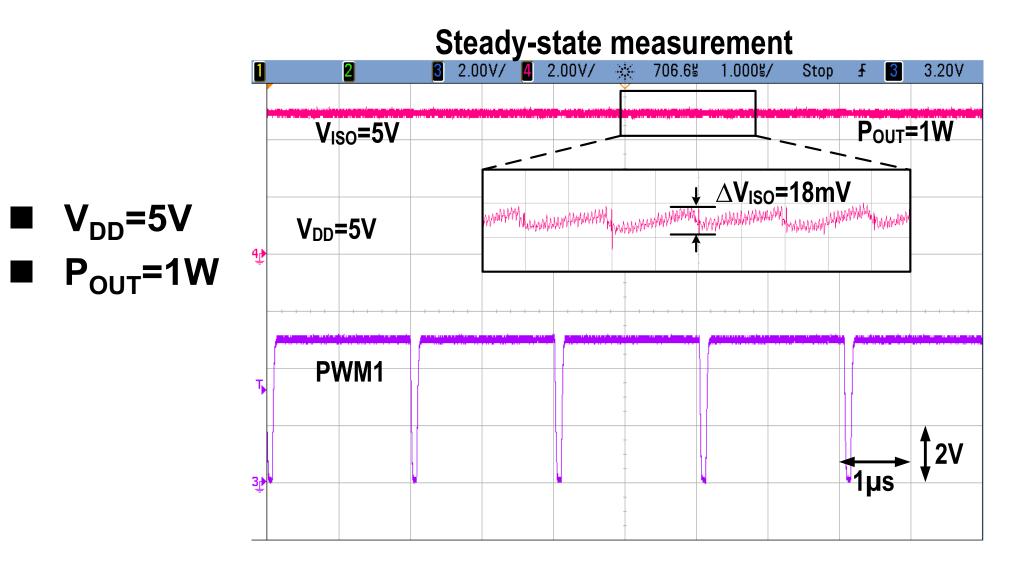


- 0.18µm BCD process
- Chip area:
- TX:0.8mm×1.45mm
- RX:1.2mm×1.45mm
- TF area:2mm×4mm
- Package area:5mm×5mm

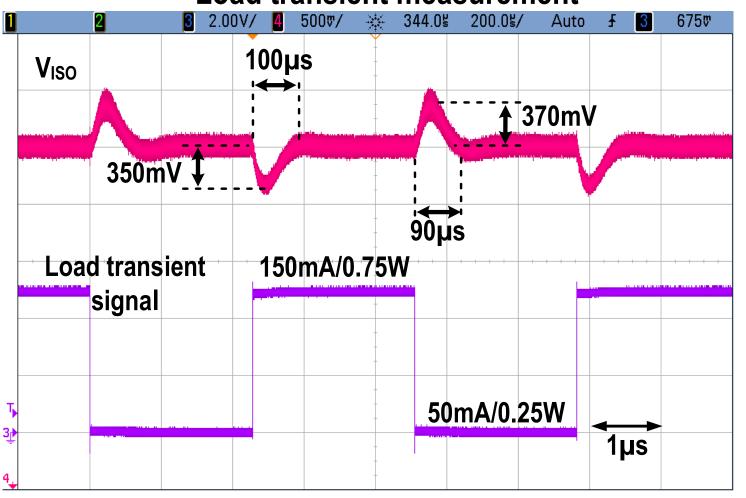


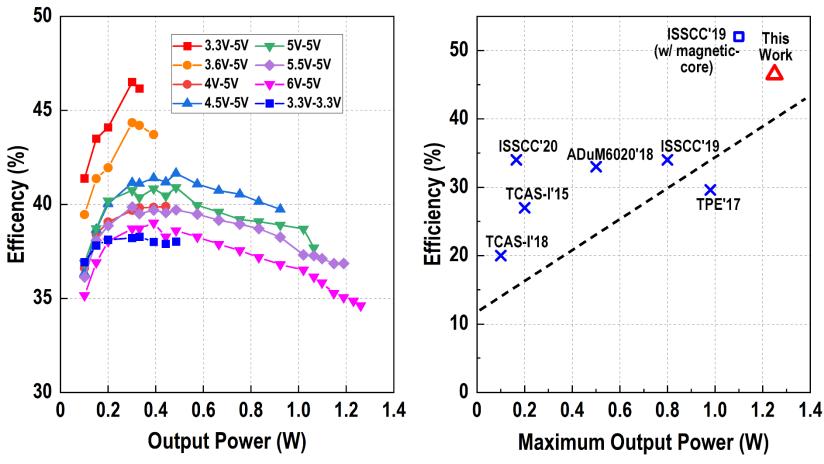












- V_{DD}/V_{ISO}=3.3V/5V: peak efficiency=46.5%@0.3W
- V_{DD}/V_{ISO}=5V/5V: efficiency>36.9%@0.1W~1.05W

Comparison

Reference	TCASI'18 [6]	ADuM6020'18 [7]	ISSCC'19 [2]	ISSCC'19 [3]	ISSCC'20 [4]	This work
Technology	0.35µm BCD	N/A	0.35µm BCD	0.35µm BCD	0.35µm BCD	0.18µm BCD
Transformer Type	Coreless	N/A	Coreless	Magnetic-Core	Coreless	Coreless
Input Voltage	3.3V	5V	4.5-5.5V	4.5-5.5V	3.3V	3-6V
Output Voltage	2.4V-3.3V	5V/3.3V	3.3V-5V	5V	3.3V	3.3V/5V
Max. P _{out}	0.093W	0.5W	0.8W	1.1W	0.165W	1.25W
Peak Efficiency	19%	33%	34%	52%	34%	46.5%
No. of Die	2	N/A	3	4	3	2
Package (Size)	N/A	SOIC-16 (10mm*13mm)	SOIC-8 (10mm*6mm)	SOIC-28 (10mm*18mm)	N/A	Glass-based FOWLP (5mm*5mm)
Power Density*	N/A	3.85mW/mm ²	13.33mW/mm ²	6.11mW/mm ²	N/A	50mW/mm ²

^{*}Power density is calculated by dividing the maximum output power by the package size

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Conclusions

- A TiP solution for isolated DC-DC converters by using glass-based FOWLP to achieve 46.5% peak efficiency and 1.25W maximum P_{OUT} in a compact 5mm×5mm package
- A high-Q transformer (TF) and the interconnections can be both formed by using RDLs without an extra TF chip, and the system only needs two dies (the Tx chip and the Rx chip)
- A varactor section in LC tank oscillator is proposed to cope with a wide V_{DD} range of 3~6V

Acknowledgments

- This work was supported in part by the National Key R&D Program of China under Grant No. 2019YFB2204800 and the Strategic Priority Research Program of Chinese Academy of Sciences under Grant No. XDB44000000
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Thank You!